





## LOW V<sub>CE(SAT)</sub> NPN SURFACE MOUNT TRANSISTOR

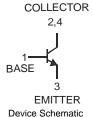
## **Features**

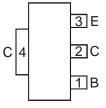
- Ideally Suited for Automated Assembly Processes
- Complementary PNP Type Available (DJT4030P)
- Low Collector-Emitter Saturation Voltage
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

## **Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.115 grams (approximate)







Pin Out Configuration

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Peak Pulse Current	I <sub>CM</sub>	5	A
Continuous Collector Current	Ic	3	A
Base Current	lΒ	1	A

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	1.2	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	104	°C/W
Power Dissipation (Note 4) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	2	W
Thermal Resistance, Junction to Ambient Air (Note 4) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	62.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### Notes:

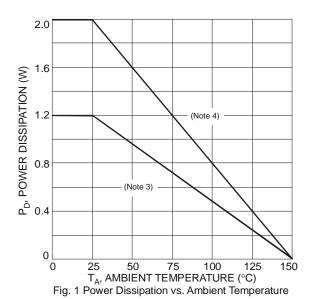
- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 4. Device mounted on FR-4 PCB with 1 inch<sup>2</sup> copper pad layout.

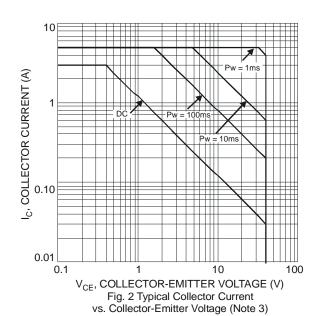


## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

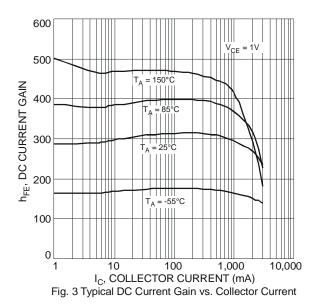
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	40	_	_	V	$I_C = 100 \mu A$	
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	40	_	_	V	I <sub>C</sub> = 10mA	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	_	_	V	$I_E = 50\mu A$	
Collector-Base Cutoff Current		_	_	100	nA	$V_{CB} = 40V, I_{E} = 0$	
Collector-Base Cuton Current	I <sub>CBO</sub>	_	_	50	μΑ	V <sub>CB</sub> = 40V, I <sub>E</sub> = 0, T <sub>A</sub> = 150°C	
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	100	nA	$V_{EB} = 6V, I_{C} = 0$	
ON CHARACTERISTICS (Note 4)							
		220	_	_		$V_{CE} = 1V, I_{C} = 0.5A$	
DC Current Gain	h <sub>FE</sub>	200	_	500	_	$V_{CE} = 1V$ , $I_C = 1A$	
		100	_	_		$V_{CE} = 1V$ , $I_C = 3A$	
		_	_	100		$I_C = 0.5A, I_B = 5mA$	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	150	mV	I <sub>C</sub> = 1A, I <sub>B</sub> = 10mA	
			300		$I_C = 3A$ , $I_B = 0.3A$		
Equivalent On-Resistance	R <sub>CE(SAT)</sub>	_	_	100	mΩ	$I_E = 3A$ , $I_B = 0.3A$	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	_	1.0	V	$I_C = 1A$ , $I_B = 0.1A$	
Base-Emitter Turn-on Voltage	V <sub>BE(ON)</sub>	_	_	1.0	V	$V_{CE} = 2V$ , $I_C = 1A$	
SMALL SIGNAL CHARACTERISTICS							
Transition Frequency	f⊤	_	105	_	MHz	$V_{CE} = 10V, I_{C} = 100mA,$ f = 100MHz	
Output Capacitance	$C_{obo}$	_	27	_	pF	V <sub>CB</sub> = 10V, f = 1MHz	
Input Capacitance	C <sub>lbo</sub>	_	180	_	pF	$V_{CB} = 5V, f = 1MHz$	
SWITCHING CHARACTERISTICS					-		
Turn-On Time	t <sub>on</sub>	_	45	_	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 2A, I <sub>B1</sub> = 200mA	
Delay Time	t <sub>d</sub>	_	14	_	ns		
Rise Time	t <sub>r</sub>	_	31	_	ns		
Turn-Off Time	t <sub>off</sub>		276	_	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 2A, I <sub>B1</sub> = I <sub>B2</sub> = 200mA	
Storage Time	ts	_	244	_	ns		
Fall Time	t <sub>f</sub>		32	_	ns		

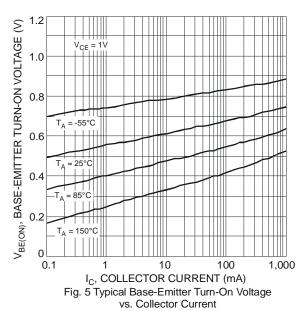
Notes: 4. Measured under pulsed conditions. Pulse width =  $300\mu$ s. Duty cycle  $\leq 2\%$ .

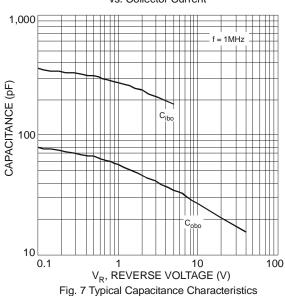












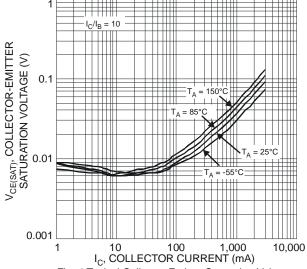


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

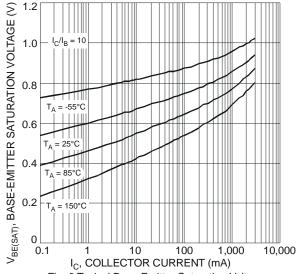


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



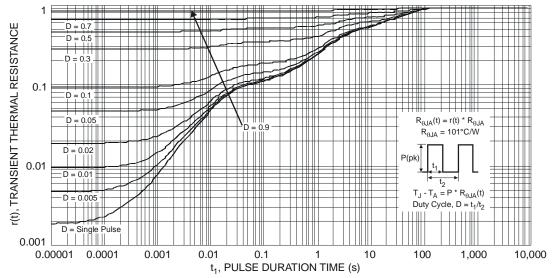


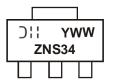
Fig. 8 Transient Thermal Response (Note 3)

## Ordering Information (Note 5)

Part Number	Case	Packaging
DJT4031N-13	SOT-223	2500/Tape & Reel

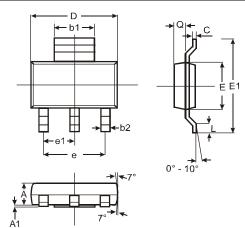
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



ZNS34 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex: 8 = 2008) WW = Week code 01 - 52

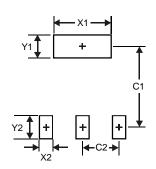
# **Package Outline Dimensions**



SOT-223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b1	2.90	3.10	3.00	
b2	0.60	0.80	0.70	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	_	_	4.60	
e1			2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All [	All Dimensions in mm			



## **Suggested Pad Layout**



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

## IMPORTANT NOTICE

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